

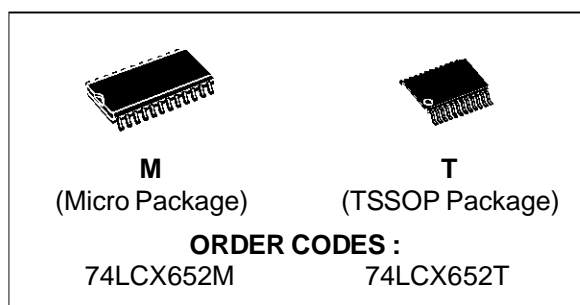
## LOW VOLTAGE CMOS OCTAL BUS TRANSCEIVER/REGISTER WITH 5V TOLERANT INPUTS AND OUTPUTS

### PRELIMINARY DATA

- 5V TOLERANT INPUTS AND OUTPUTS
- HIGH SPEED:  
 $t_{PD} = 7.0 \text{ ns (MAX.)}$  at  $V_{CC} = 3V$
- POWER-DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 24 \text{ mA (MIN)}$
- PCI BUS LEVELS GUARANTEED AT 24mA
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \equiv t_{PHL}$
- OPERATING VOLTAGE RANGE:  
 $V_{CC} \text{ (OPR)} = 2.0V \text{ to } 3.6V$  (1.5V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 652
- LATCH-UP PERFORMANCE EXCEEDS 500mA
- ESD PERFORMANCE:  
HBM > 2000V; MM > 200V

### DESCRIPTION

The LCX652 is a low voltage CMOS OCTAL BUS TRANSCEIVERS AND REGISTERS (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology. It is ideal for low power and high speed 3.3V applications; it can be interfaced to 5V signal environment for both inputs and outputs.

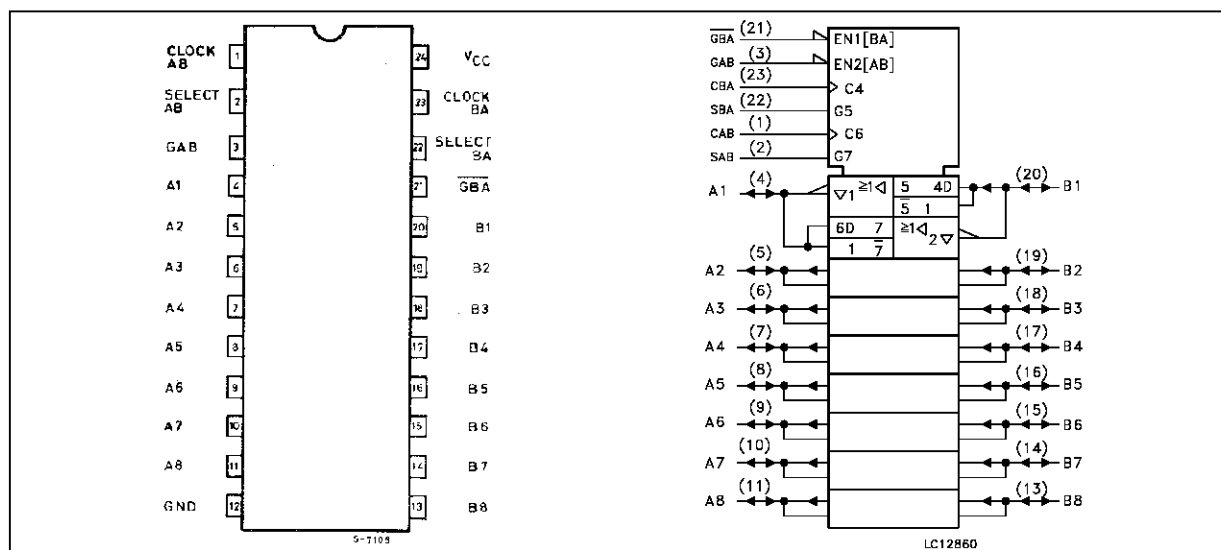


This device consists of bus transceiver circuits with 3-state output, D type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal storage registers. Enable (GAB) and (GBA) pins are provided to control the transceiver functions.

Select AB and Select BA control pins are provided to select whether real-time or stored data is transferred. A low input level selects real-time, and a high selects stored data.

Data on the A or B bus, or both, can be stored in the internal D flip-flop by low-to-high transitions at the appropriate clock pins (CLOCK AB or CLOCK BA) regardless of the select or enable control

### PIN CONNECTION AND IEC LOGIC SYMBOLS

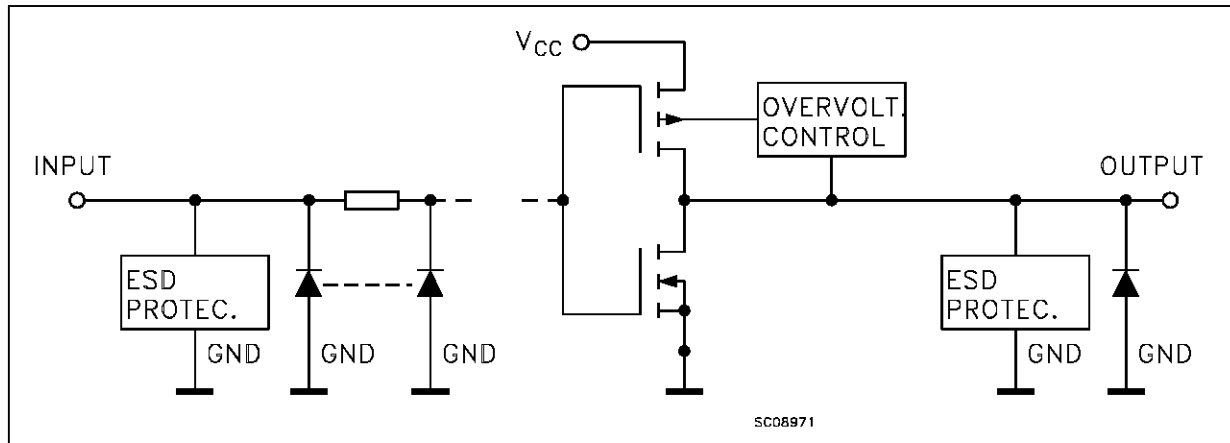


pins. When select AB and select BA are in the real-time transfer mode, it is also possible to store data without using the internal D-type flip-flops by simultaneously enabling GAB or GBA. In this configuration each output reinforces its input. It has same speed performance at 3.3V than 5V,

AC/ACT family, combined with a lower power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

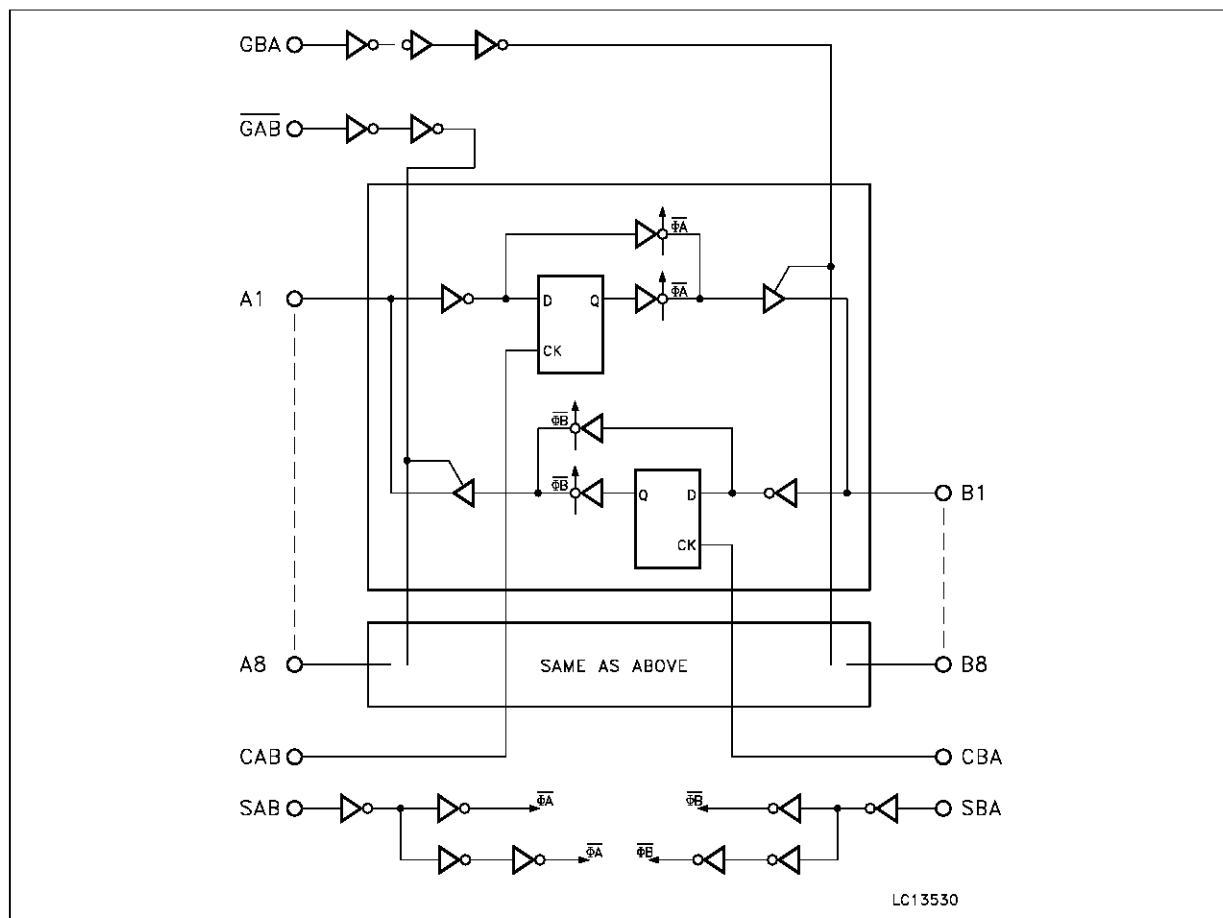
#### INPUT AND OUTPUT EQUIVALENT CIRCUIT



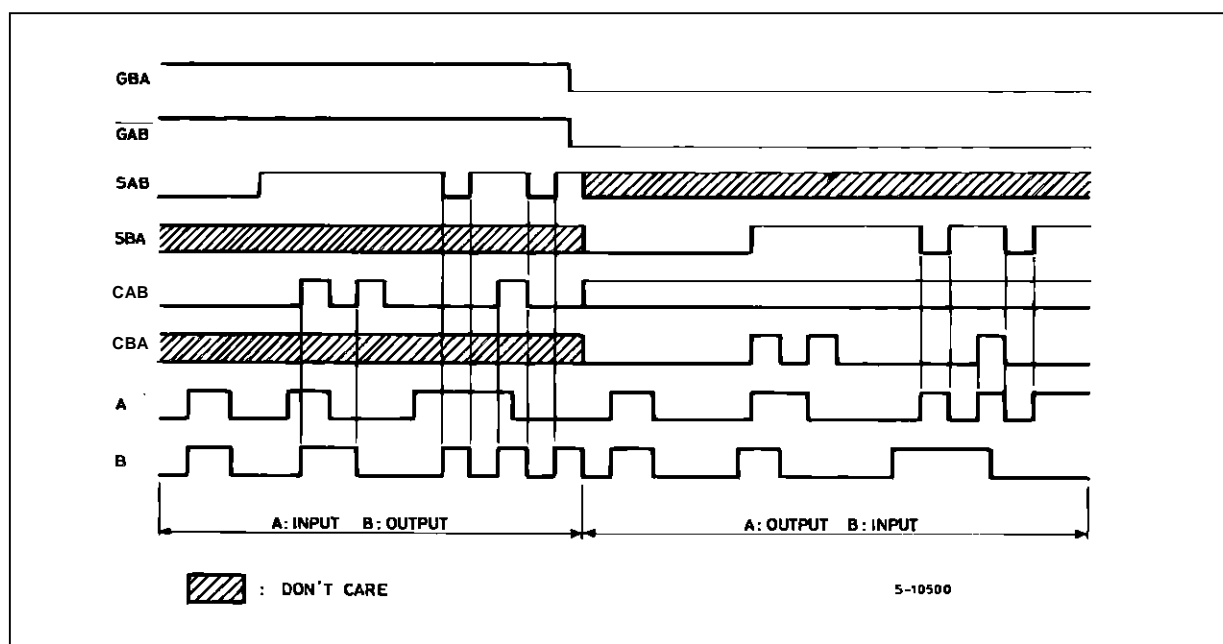
#### PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	CAB	A to B Clock Input (LOW to HIGH, Edge-Triggered)
2	SAB	Select A to B Source Input
3	GAB	Direction Control Input
4, 5, 6, 7, 8, 9, 10, 11	A1 to A8	A Data Inputs/Outputs
20, 19, 18, 17, 16, 15, 14, 13	B1 to B8	B Data Inputs/Outputs
21	GBA	Output Enable Input (Active LOW)
22	SBA	Select B to A Source Input
23	CBA	B to A Clock Input (LOW to HIGH, Edge-Triggered)
12	GND	Ground (0V)
24	V <sub>CC</sub>	Positive Supply Voltage







## LOGIC DIAGRAM



## TIMING CHART



## TRUTH TABLE

GAB	GBA	CAB	CBA	SAB	SBA	A	B	FUNCTION
L	H					INPUTS	INPUTS	Both the A bus and the B bus are inputs
		X	X	X	X	Z	Z	The output functions of the A and B bus are disabled
				X	X	INPUTS	INPUTS	Both the A and B busses are used as inputs to the internal flip-flops. Data on the bus will be stored on low to high transition of the clock inputs
L	L					OUTPUTS	INPUTS	The A bus are outputs and the B bus are inputs
		X*	X	X	L	L	L	The data on the B bus are displayed on the A bus
						H	H	
		X*		X	L	L	L	The data on the B bus are displayed on the A bus and are stored in the B internal flip-flop on low to high transition of the clock pulse
						H	H	
		X*	X	X	H	Qn	X	The data stored in the B internal flip-flop are displayed on the A bus
		X*		X	H	L	L	The data on the B bus are stored in the B internal flip-flop on low to high transition of the clock pulse. The states of the internal flip-flops propagate directly to the A bus
						H	H	
H	H					INPUTS	OUTPUTS	The A bus are inputs and the B bus are outputs
		X	X*	L	X	L	L	The data on the A bus are displayed on the B bus
						H	H	
			X*	L	X	L	L	The data on the A bus are displayed on the B bus and are stored in the A internal flip-flop on low to high transition of the clock pulse
						H	H	
		X	X*	H	X	X	Qn	The data stored in the A internal flip-flops are displayed on the B bus
			X*	H	X	L	L	The data on the A bus are stored in the A internal flip-flop on low to high transition of the clock pulse. The states of the internal flip-flops propagate directly on the B bus
						H	H	
H	L					OUTPUTS	OUTPUTS	Both the A bus and the B bus are outputs
		X	X	H	H	Qn	Qn	The data stored in the internal flip-flops are displayed on the A and B bus respectively

X : DON'T CARE

Z : HIGH IMPEDANCE

Qn : THE DATA STORED TO THE INTERNAL FLIP-FLOPS BY MOST RECENT LOW TO HIGH TRANSITION OF THE CLOCK INPUTS

\* : THE DATA AT THE A AND B BUS WILL BE STORED TO THE INTERNAL FLIP-FLOPS ON EVERY LOW TO HIGH TRANSITION OF THE CLOCK INPUTS

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to + 7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 to + 7.0	V
V <sub>O</sub>	DC Output Voltage (V <sub>CC</sub> =0V)	-0.5 to + 7.0	V
V <sub>O</sub>	DC Output Voltage (High or Low State) (note1)	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 50	mA
I <sub>OK</sub>	DC Output Diode Current (note2)	± 50	mA
I <sub>O</sub>	DC Output Source/Sink Current	± 50	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin	± 100	mA
I <sub>GND</sub>	DC Ground Current per Supply Pin	± 100	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

1) I<sub>O</sub> absolute maximum rating must be observed

2) V<sub>O</sub> < GND, V<sub>O</sub> > V<sub>CC</sub>

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage (note 1)	2.0 to 3.6	V
V <sub>I</sub>	Input Voltage	0 to 5.5	V
V <sub>O</sub>	Output Voltage (V <sub>CC</sub> =0V)	0 to 5.5	V
V <sub>O</sub>	Output Voltage (High or Low State)	0 to V <sub>CC</sub>	V
I <sub>OH</sub> , I <sub>OL</sub>	High or Low Level Output Current (V <sub>CC</sub> = 3.0 to 3.6V)	± 24	mA
I <sub>OH</sub> , I <sub>OL</sub>	High or Low Level Output Current (V <sub>CC</sub> = 2.7 to 3.0V)	± 12	mA
T <sub>op</sub>	Operating Temperature:	-40 to +85	°C
dt/dv	Input Transition Rise or Fall Rate (V <sub>CC</sub> = 3.0V) (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.5V to 3.6V

2) V<sub>IN</sub> from 0.8V to 2.0V

## DC SPECIFICATIONS

Symbol	Parameter	Test Conditions			Value		Unit
		V <sub>CC</sub> (V)		-40 to 85 °C			
				Min.	Max.		
V <sub>IH</sub>	High Level Input Voltage	2.7 to 3.6			2.0		V
V <sub>IL</sub>	Low Level Input Voltage					0.8	
V <sub>OH</sub>	High Level Output Voltage	2.7 to 3.6	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>O</sub> =-100 μA	V <sub>CC</sub> -0.2		V
		2.7		I <sub>O</sub> =-12 mA	2.2		
		3.0		I <sub>O</sub> =-18 mA	2.4		
				I <sub>O</sub> =-24 mA	2.2		
V <sub>OL</sub>	Low Level Output Voltage	2.7 to 3.6	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>O</sub> =100 μA		0.2	V
		2.7		I <sub>O</sub> =12 mA		0.4	
		3.0		I <sub>O</sub> =16 mA		0.4	
		3.0		I <sub>O</sub> =24 mA		0.55	
I <sub>I</sub>	Input Leakage Current	2.7 to 3.6	V <sub>I</sub> = 0 to 5.5 V			±5	μA
I <sub>OZ</sub>	3 State Output Leakage Current	2.7 to 3.6	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>O</sub> = 0 to 5.5V			±5	μA
I <sub>off</sub>	Power Off Leakage Current	0	V <sub>I</sub> or V <sub>O</sub> = 5.5V			100	μA
I <sub>CC</sub>	Quiescent Supply Current	2.7 to 3.6	V <sub>I</sub> = V <sub>CC</sub> or GND			10	μA
			V <sub>I</sub> or V <sub>O</sub> = 3.6 to 5.5V			±10	
ΔI <sub>CC</sub>	ICC incr. per input	2.7 to 3.6	V <sub>IH</sub> = V <sub>CC</sub> -0.6V			500	μA

## DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value			Unit
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25 °C			
				Min.	Typ.	Max.	
V <sub>OLP</sub>	Dynamic Low Voltage Quiet Output (note 1)	3.3	C <sub>L</sub> = 50 pF V <sub>IL</sub> = 0 V V <sub>IH</sub> = 3.3V		0.8		V
V <sub>OLV</sub>					-0.8		

1) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the LOW state.

**AC ELECTRICAL CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ ,  $R_L = 500 \Omega$ , Input  $t_r = t_f = 2.5 \text{ ns}$ )

Symbol	Parameter	Test Condition		Value		Unit
		V <sub>CC</sub> (V)	Waveform	-40 to 85 °C		
				Min.	Max.	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time CK to Q or $\overline{Q}$	2.7 3.0 to 3.6	1	1.5 1.5	9.5 8.5	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time An or Bn to Q or $\overline{Q}$	2.7 3.0 to 3.6	1	1.5 1.5	8.0 7.0	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time SELECT to Q or $\overline{Q}$	2.7 3.0 to 3.6	1	1.5 1.5	9.5 8.5	ns
t <sub>PZL</sub> t <sub>PZH</sub>	Output Enable Time	2.7 3.0 to 3.6	2	1.5 1.5	9.5 8.5	ns
t <sub>PLZ</sub> t <sub>PHZ</sub>	Output Disable Time	2.7 3.0 to 3.6	2	1.5 1.5	9.5 8.5	ns
t <sub>s</sub>	Setup Time, HIGH or LOW Level Data to Ck	2.7 3.0 to 3.6	1	2.5 2.5		ns
t <sub>h</sub>	Hold Time, HIGH or LOW Level Data to Ck	2.7 3.0 to 3.6	1	1.5 1.5		ns
t <sub>w</sub>	CK Pulse Width, HIGH or LOW	2.7 3.0 to 3.6	3	4.0 3.3		ns
f <sub>MAX</sub>	Clock Pulse Frequency	3.0 to 3.6	1	150		MHz
t <sub>OSLZ</sub> t <sub>OSHL</sub>	Output to Output Skew Time (note 1, 2)	3.0 to 3.6			1.0	ns

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ( $t_{OSLH} = |t_{PLHm} - t_{PLHn}|$ ,  $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$ )

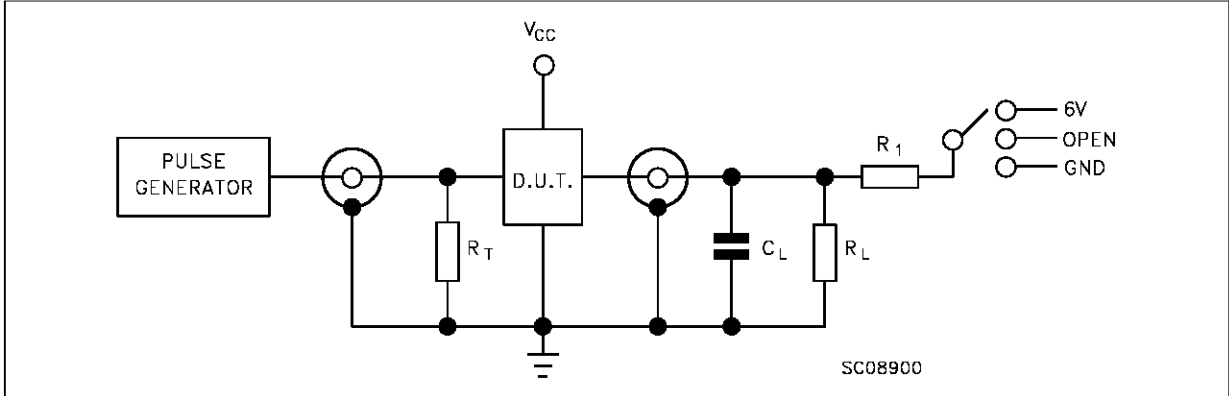
2) Parameter guaranteed by design

**CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Value			Unit
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25 °C			
				Min.	Typ.	Max.	
C <sub>IN</sub>	Input Capacitance	3.3	V <sub>IN</sub> = 0 to V <sub>CC</sub>		6		pF
C <sub>i/o</sub>	I/O Capacitance	3.3	V <sub>IN</sub> = 0 to V <sub>CC</sub>		10		pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	3.3	f <sub>IN</sub> = 10MHz V <sub>IN</sub> = 0 or V <sub>CC</sub>		TBD		pF

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/n$  (per circuit)

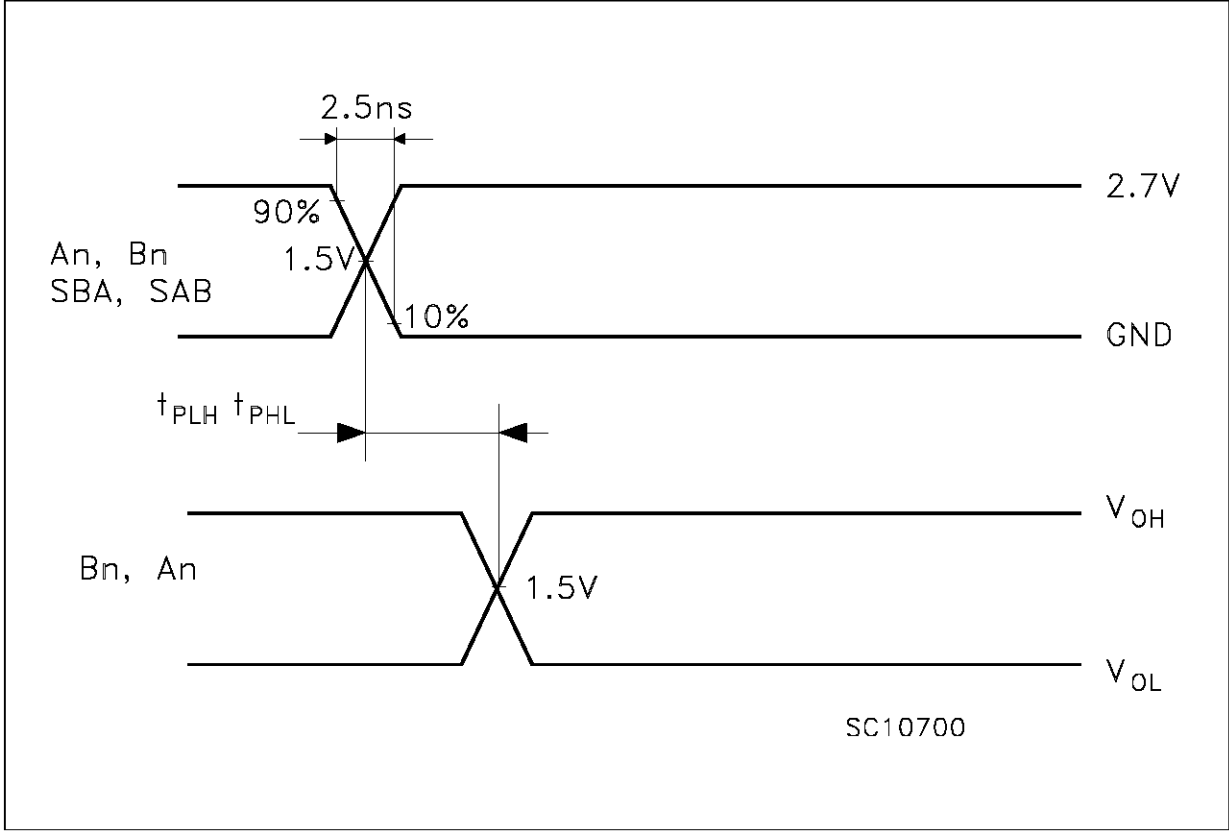
TEST CIRCUIT



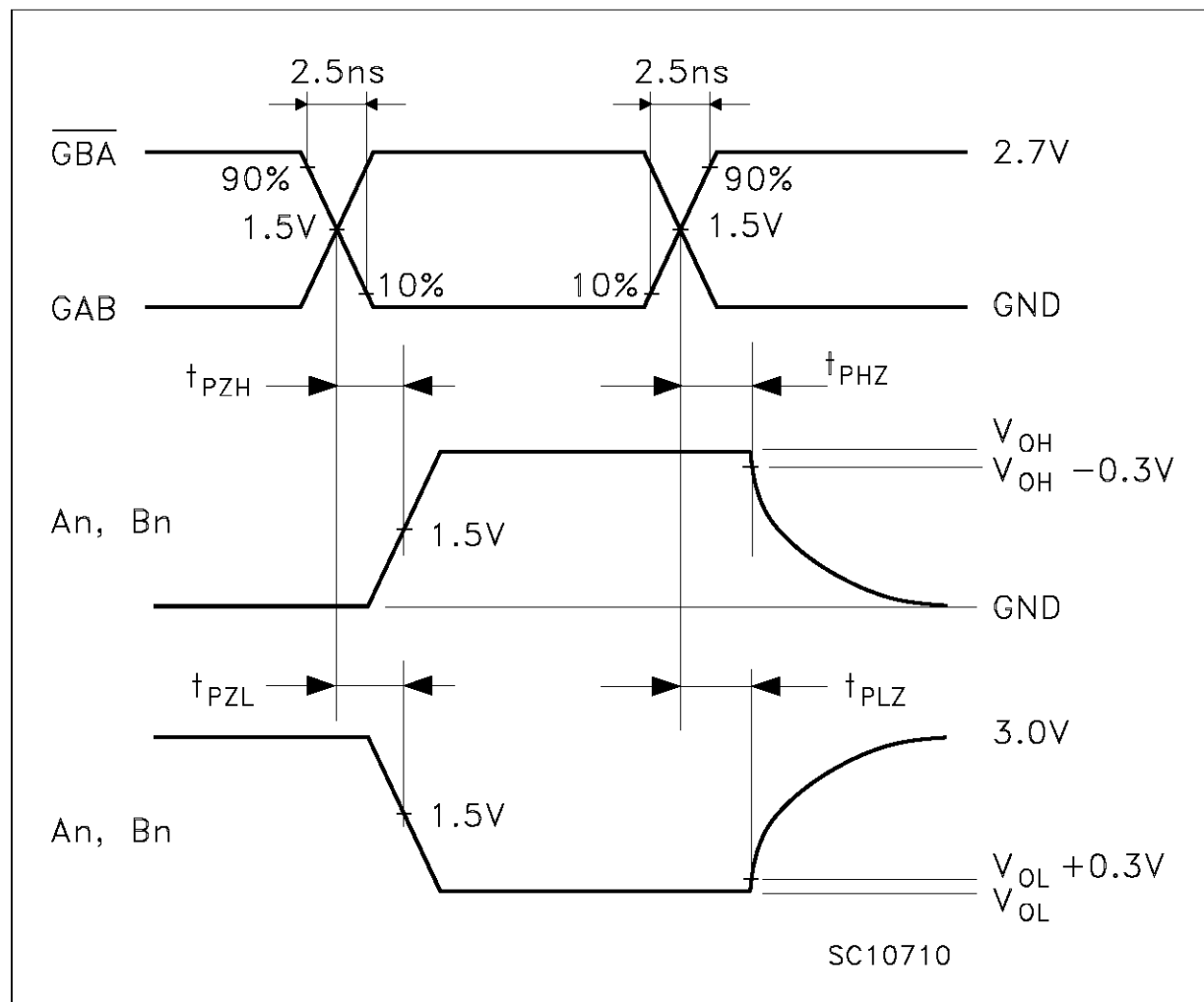
TEST	SWITCH
$t_{PLH}$ , $t_{PHL}$	Open
$t_{PZL}$ , $t_{PLZ}$	6V
$t_{PZH}$ , $t_{PHZ}$	GND

$C_L$  = 50 pF or equivalent (includes jig and probe capacitance)  
 $R_L = R_1$  = 500 $\Omega$  or equivalent  
 $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )

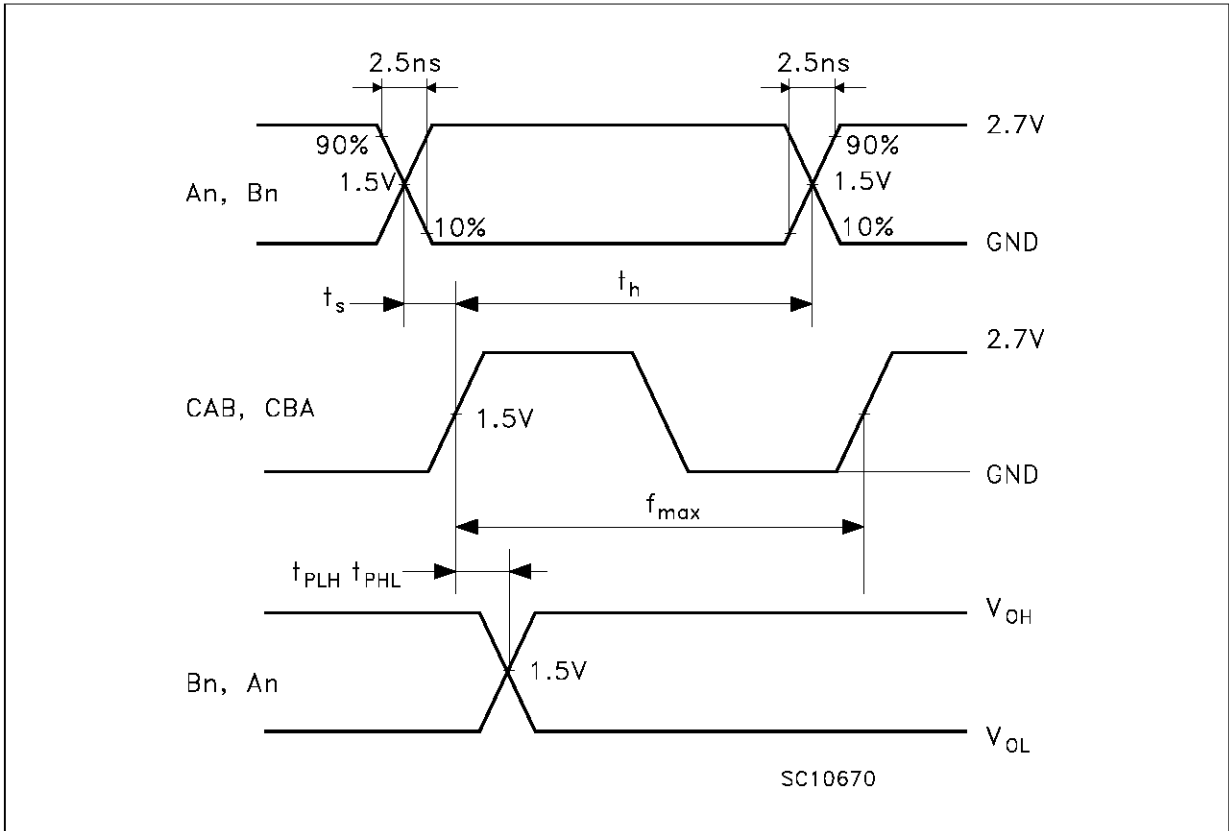
WAVEFORM 1: PROPAGATION DELAYS, SAB, SBA, An, Bn TIMES (f=1MHz; 50% duty cycle)



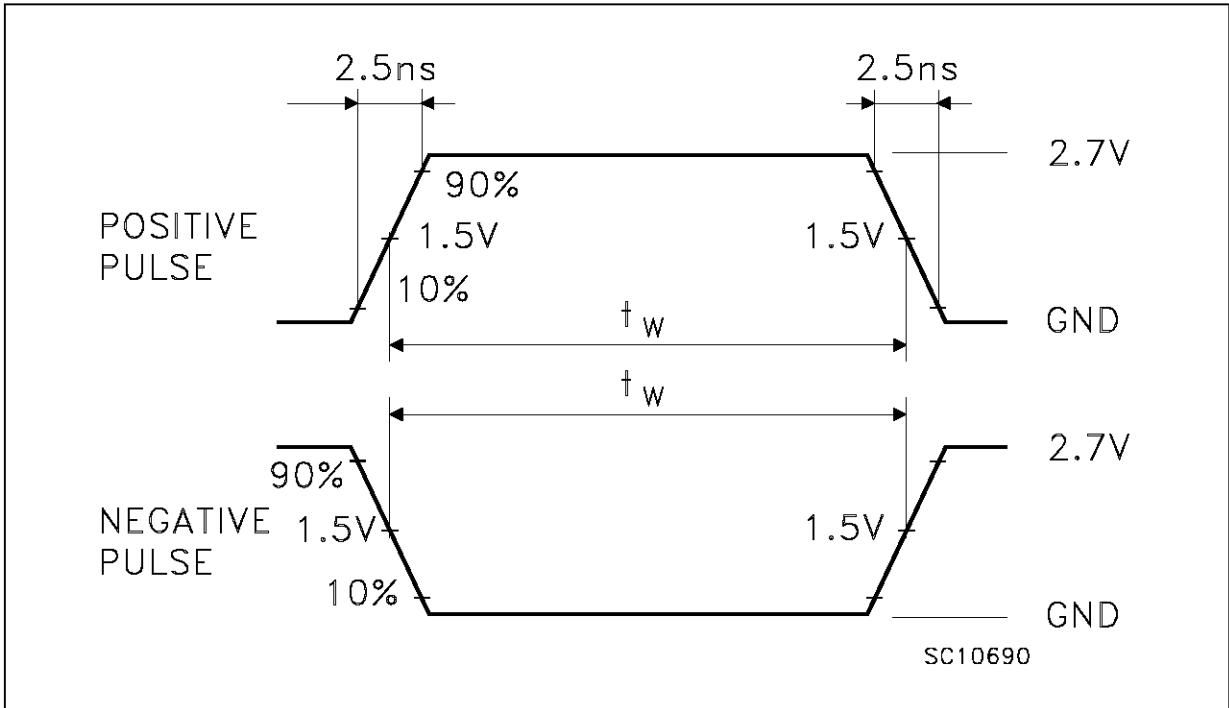


**WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIMES** ( $f=1\text{MHz}$ ; 50% duty cycle)

WAVEFORM 3: PROPAGATION DELAY TIMES ( $f=1\text{MHz}$ ; 50% duty cycle)

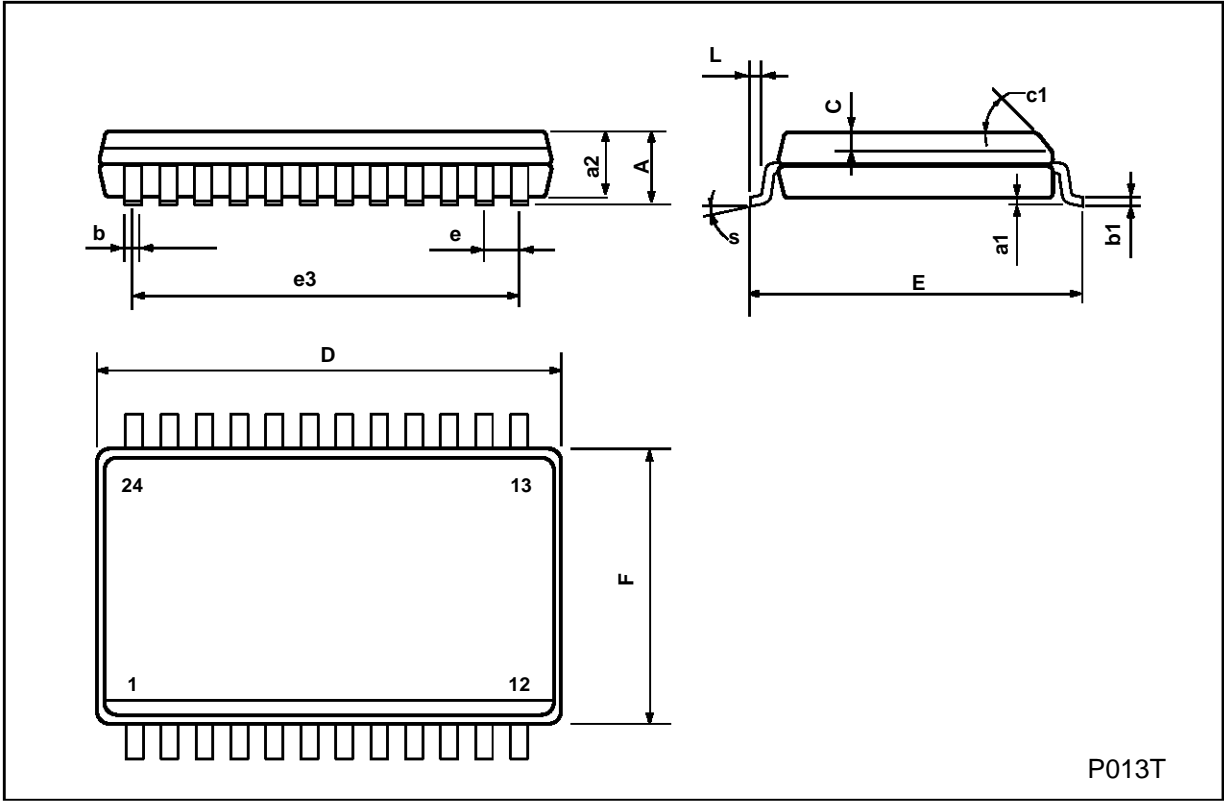


WAVEFORM 4: PULSE WIDTH



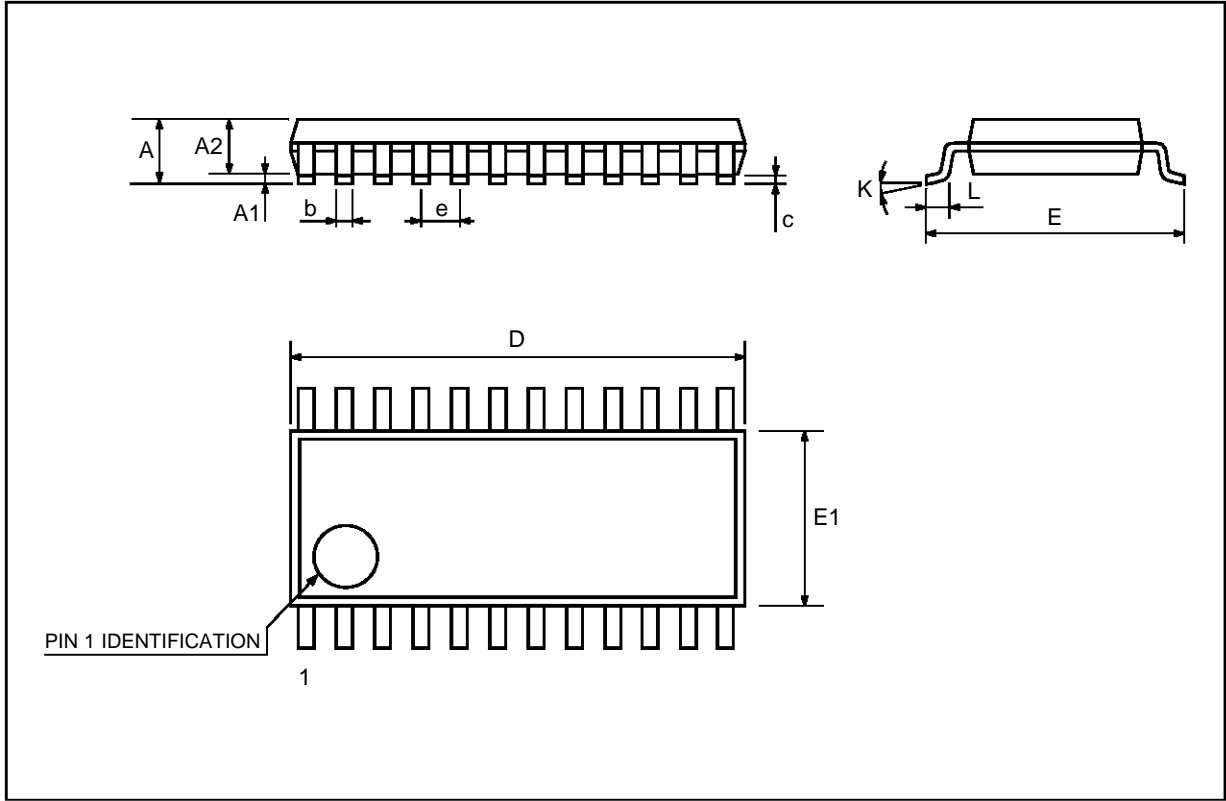
SO24 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45 (typ.)					
D	15.20		15.60	0.598		0.614
E	10.00		10.65	0.393		0.420
e		1.27			0.05	
e3		13.97			0.55	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
S	8 (max.)					



TSSOP24 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.1			0.433
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.85	0.9	0.95	0.335	0.354	0.374
b	0.19		0.30	0.0075		0.0118
c	0.09		0.2	0.0035		0.0079
D	7.7	7.8	7.9	0.303	0.307	0.311
E	6.25	6.4	6.5	0.246	0.252	0.256
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°	4°	8°	0°	4°	8°
L	0.50	0.60	0.70	0.020	0.024	0.028



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